

# DATA SHEET

## **PDTC114Y series**

**NPN resistor-equipped transistors;**

**R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$**

Product data sheet  
Supersedes data of 2003 Sep 10

2004 Aug 17

## NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

## PDTC114Y series

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	–	50	V
I <sub>O</sub>	output current (DC)	–	100	mA
R1	bias resistor	10	–	k $\Omega$
R2	bias resistor	47	–	k $\Omega$

### DESCRIPTION

NPN resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	PNP COMPLEMENT
	PHILIPS	EIAJ		
PDTC114YE	SOT416	SC-75	33	PDTA114YE
PDTC114YEF	SOT490	SC-89	12	PDTA114YEF
PDTC114YK	SOT346	SC-59	47	PDTA114YK
PDTC114YM	SOT883	SC-101	DU	PDTA114YM
PDTC114YS	SOT54 (TO-92)	SC-43	TC114Y	PDTA114YS
PDTC114YT	SOT23	–	*27 <sup>(1)</sup>	PDTA114YT
PDTC114YU	SOT323	SC-70	*30 <sup>(1)</sup>	PDTA114YU

### Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

NPN resistor-equipped transistors;  
 R1 = 10 kΩ, R2 = 47 kΩ

PDTC114Y series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTC114YS		1 2 3	base collector emitter
PDTC114YE PDTC114YEF PDTC114YK PDTC114YT PDTC114YU		1 2 3	base emitter collector
PDTC114YM		1 2 3	base emitter collector

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## PDTTC114Y series

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CB0</sub>	collector-base voltage	open emitter	–	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	10	V
V <sub>I</sub>	input voltage				
		positive	–	+40	V
	negative		–	–6	V
I <sub>O</sub>	output current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT416	note 1	–	150	mW
	SOT883	notes 2 and 3	–	250	mW
SOT490	notes 1 and 2	–	250	mW	
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**Notes**

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT883	notes 2 and 3	500	K/W
SOT490	notes 1 and 2	500	K/W	

**Notes**

1. Refer to standard mounting conditions.
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3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

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PDTC114Y series

**CHARACTERISTICS**

T<sub>amb</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0	–	–	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0	–	–	1	$\mu$ A
		V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0; T <sub>j</sub> = 150 °C	–	–	50	$\mu$ A
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	–	–	150	$\mu$ A
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA	100	–	–	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 5 mA; I <sub>B</sub> = 0.25 mA	–	–	100	mV
V <sub>i(off)</sub>	input-off voltage	I <sub>C</sub> = 100 $\mu$ A; V <sub>CE</sub> = 5 V	–	0.7	0.5	V
V <sub>i(on)</sub>	input-on voltage	I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 0.3 V	1.4	0.8	–	V
R1	input resistor		7	10	13	k $\Omega$
$\frac{R2}{R1}$	resistor ratio		3.7	4.7	5.7	
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz	–	–	2.5	pF

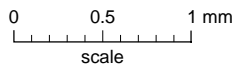
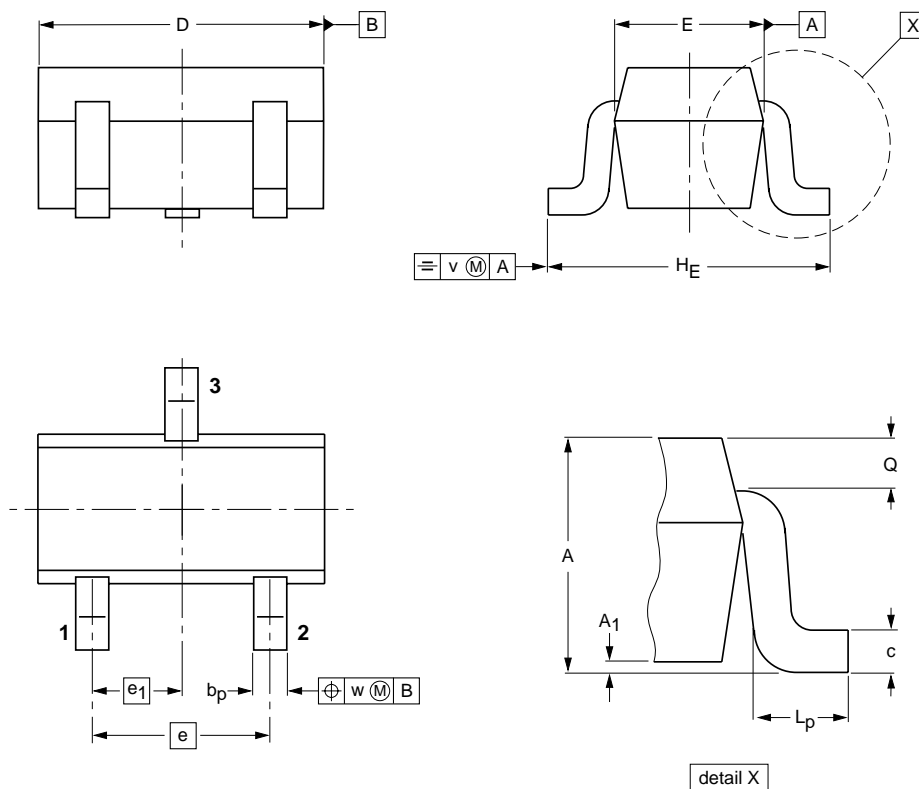
NPN resistor-equipped transistors;  
R1 = 10 kΩ, R2 = 47 kΩ

PDTC114Y series

PACKAGE OUTLINES

Plastic surface-mounted package; 3 leads

SOT416



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

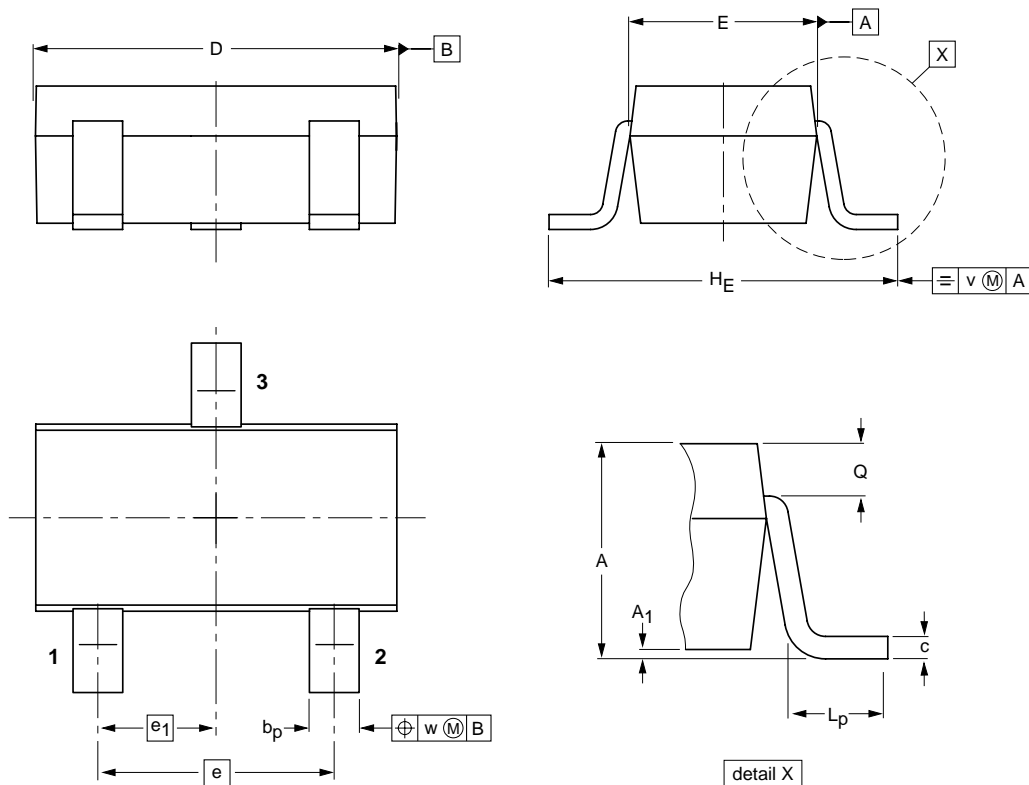
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	IEC	JEDEC	JEITA			
SOT416			SC-75			04-11-04 06-03-16

NPN resistor-equipped transistors;  
R1 = 10 kΩ, R2 = 47 kΩ

PDTC114Y series

Plastic surface-mounted package; 3 leads

SOT346



**DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

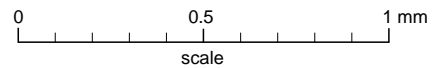
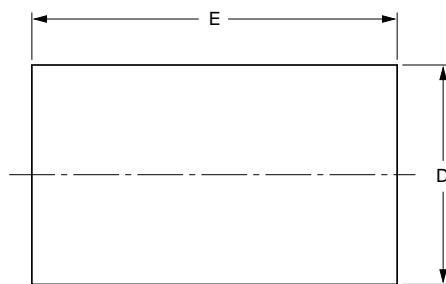
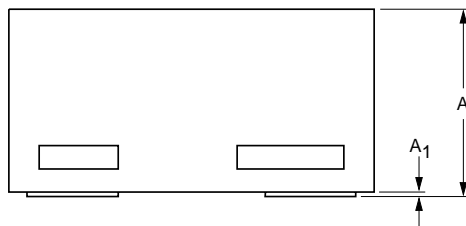
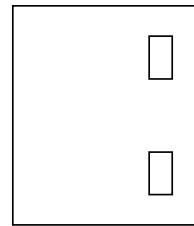
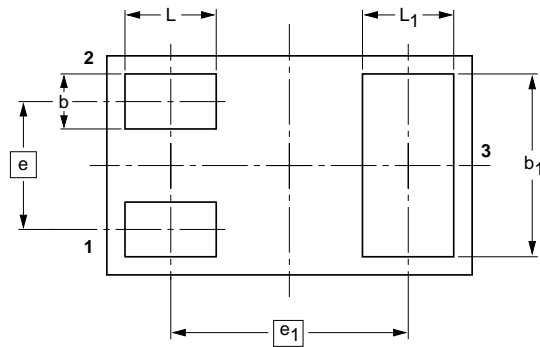
OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT346		TO-236	SC-59A		04-11-11 06-03-16

NPN resistor-equipped transistors;  
R1 = 10 kΩ, R2 = 47 kΩ

PDTC114Y series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



**DIMENSIONS (mm are the original dimensions)**

UNIT	A <sup>(1)</sup>	A <sub>1</sub> max.	b	b <sub>1</sub>	D	E	e	e <sub>1</sub>	L	L <sub>1</sub>
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

**Note**

1. Including plating thickness

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT883			SC-101		03-02-05 03-04-03

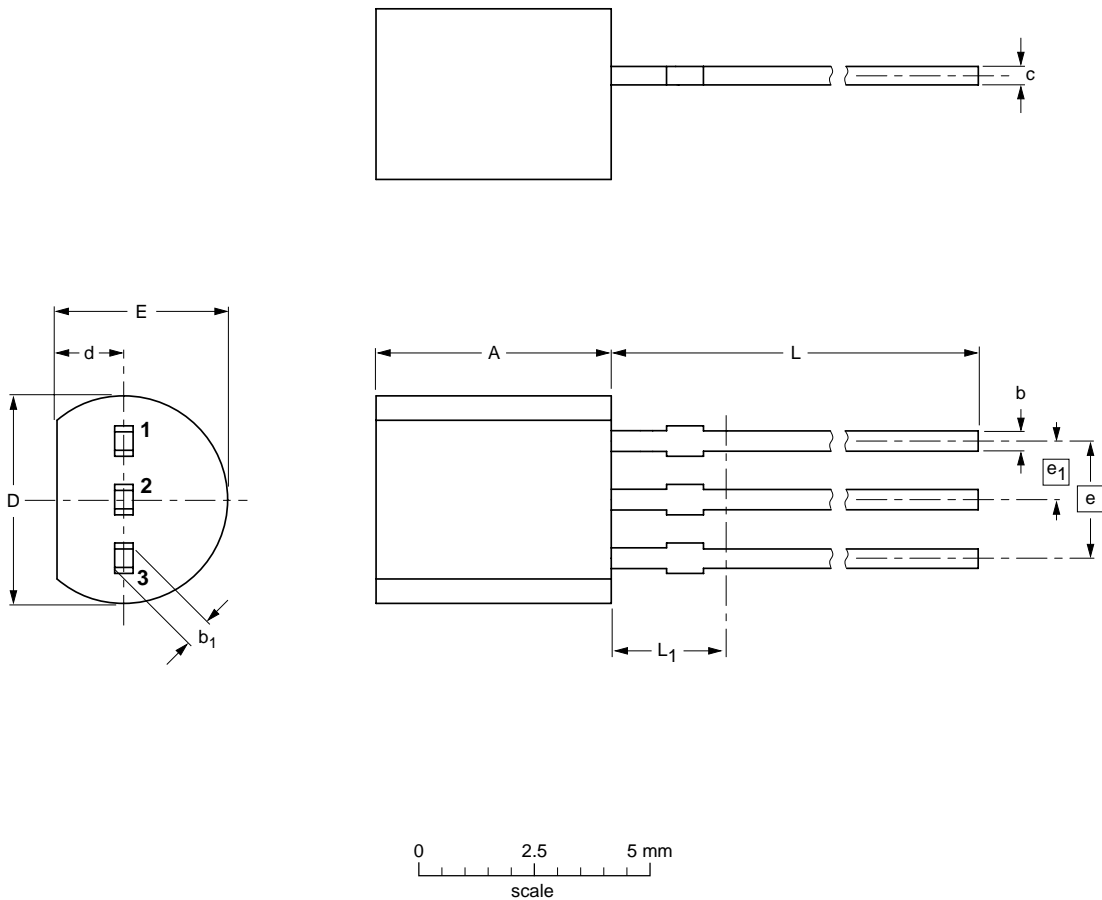


NPN resistor-equipped transistors;  
R1 = 10 kΩ, R2 = 47 kΩ

PDTC114Y series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	b	b <sub>1</sub>	c	D	d	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

**Note**

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

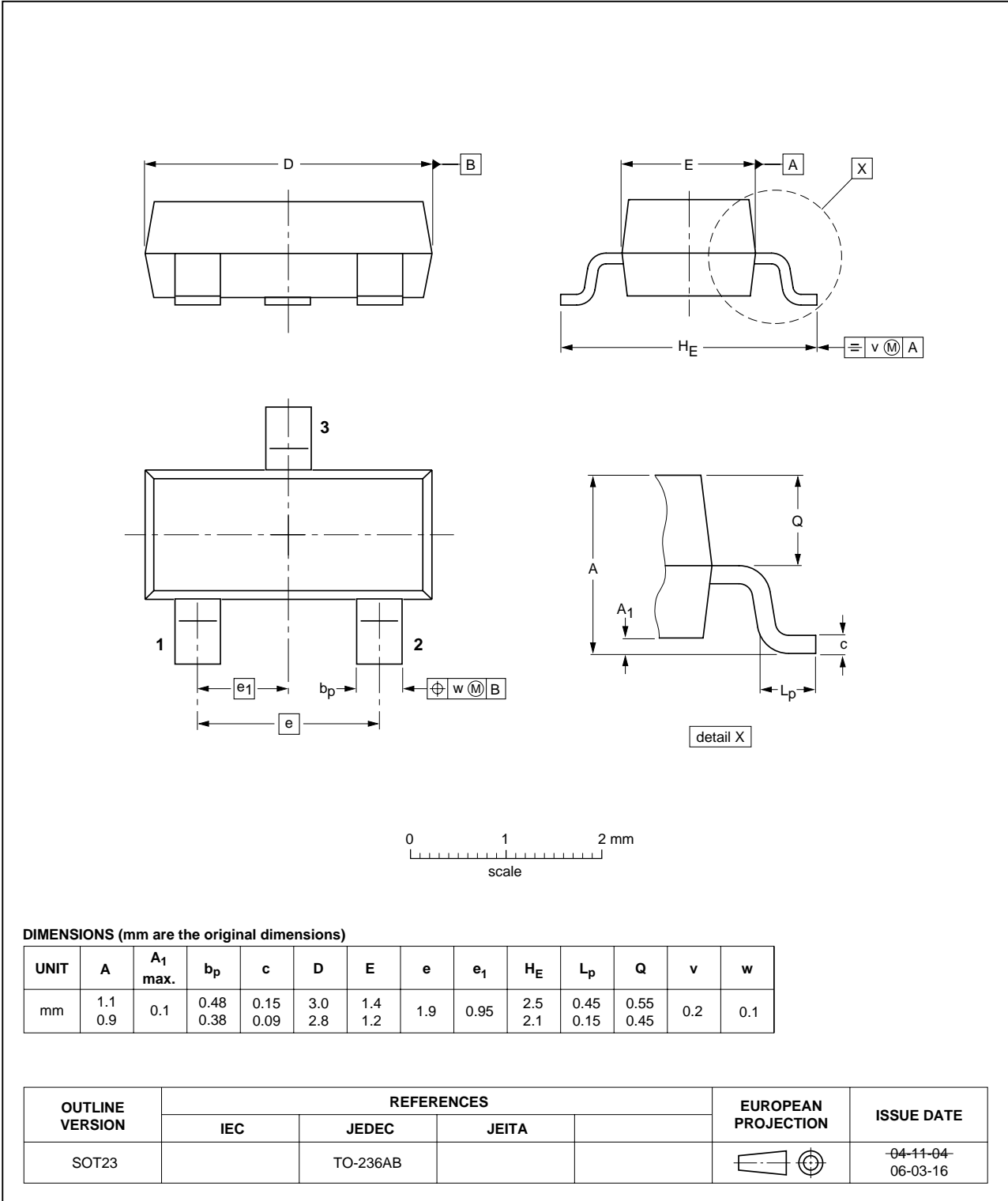
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	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		04-06-28 04-11-16

NPN resistor-equipped transistors;  
R1 = 10 kΩ, R2 = 47 kΩ

PDTC114Y series

Plastic surface-mounted package; 3 leads

SOT23

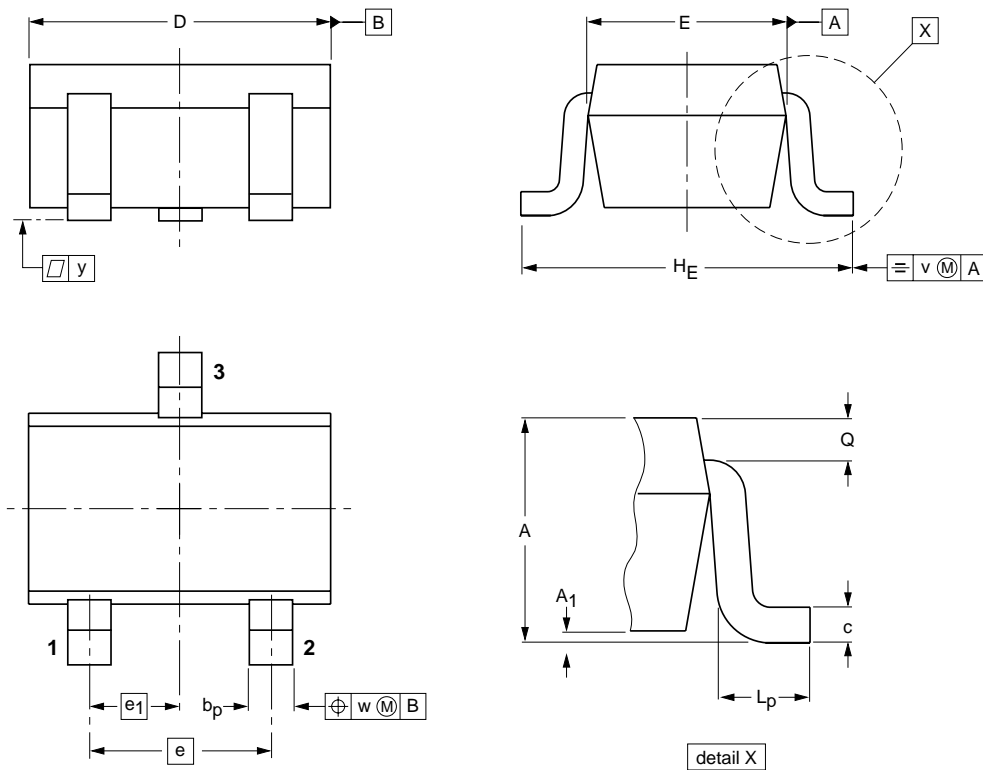


NPN resistor-equipped transistors;  
R1 = 10 kΩ, R2 = 47 kΩ

PDTC114Y series

Plastic surface-mounted package; 3 leads

SOT323



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

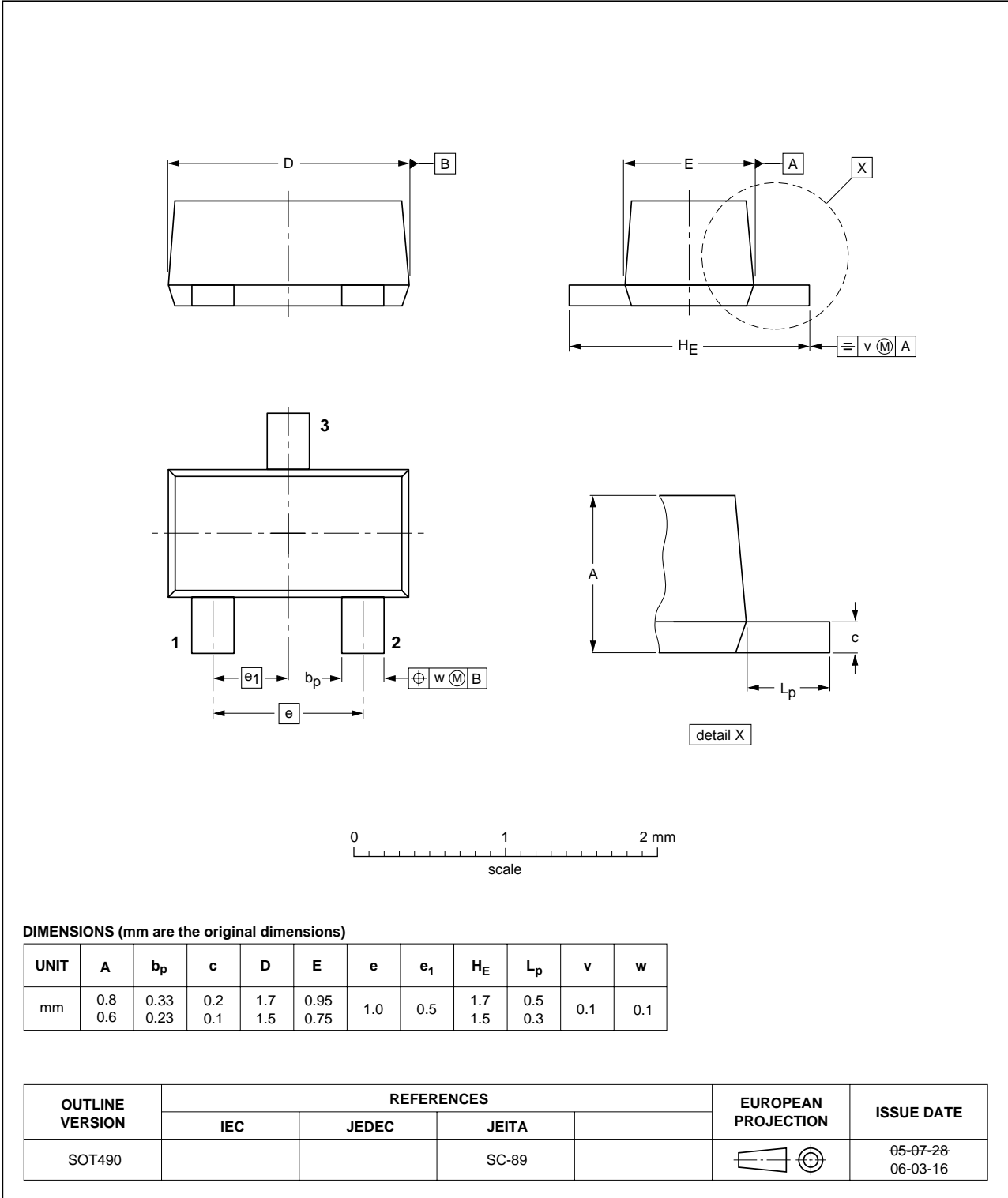
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	IEC	JEDEC	JEITA			
SOT323			SC-70			<del>04-11-04</del> 06-03-16

NPN resistor-equipped transistors;  
R1 = 10 kΩ, R2 = 47 kΩ

PDTC114Y series

Plastic surface-mounted package; 3 leads

SOT490



**NPN resistor-equipped transistors;**  
**R1 = 10 kΩ, R2 = 47 kΩ**

**PDTC114Y series**

**DATA SHEET STATUS**

<b>DOCUMENT STATUS<sup>(1)</sup></b>	<b>PRODUCT STATUS<sup>(2)</sup></b>	<b>DEFINITION</b>
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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